

NP04501

Silicon NPN epitaxial planar type

For general amplification

■ Features

- Two elements incorporated into one package (Each transistor is separated)
- SSS Mini type 6-pin package, reduction of the mounting area and assembly cost by one half
- Maximum package height (0.4 mm) contributes to develop thinner equipments

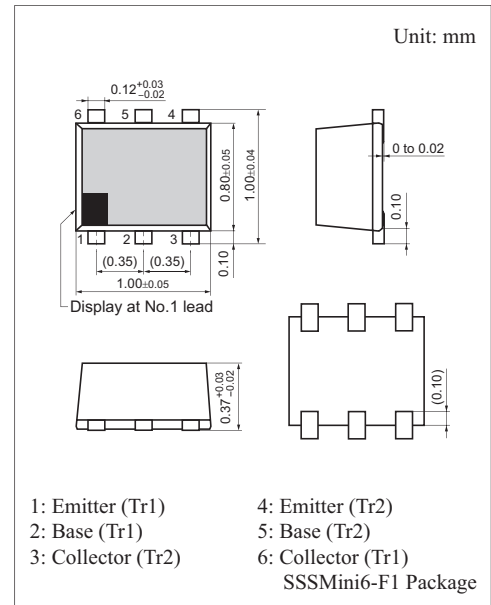
■ Basic Part Number

- 2SD0601A × 2

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

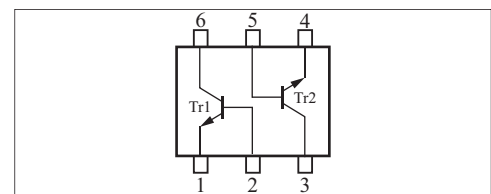
| Parameter | Symbol | Rating | Unit |
|---------------------------------------|-----------|-------------|------------------|
| Collector-base voltage (Emitter open) | V_{CBO} | 60 | V |
| Collector-emitter voltage (Base open) | V_{CEO} | 50 | V |
| Emitter-base voltage (Collector open) | V_{EBO} | 7 | V |
| Collector current | I_C | 100 | mA |
| Peak collector current | I_{CP} | 200 | mA |
| Total power dissipation * | P_T | 125 | mW |
| Junction temperature | T_j | 125 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +125 | $^\circ\text{C}$ |

Note) * : Measuring on substrate at 17 mm × 10 mm × 1 mm



Marking Symbol: 5H

Internal Connection

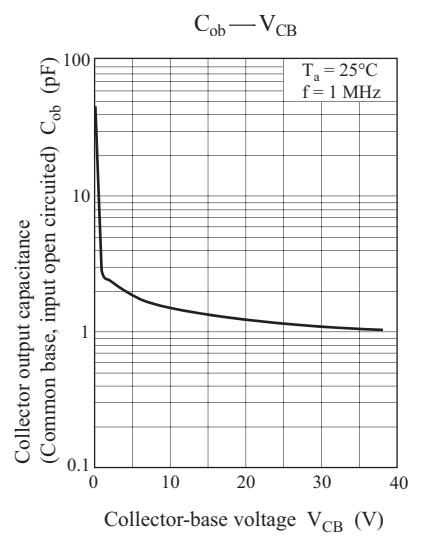
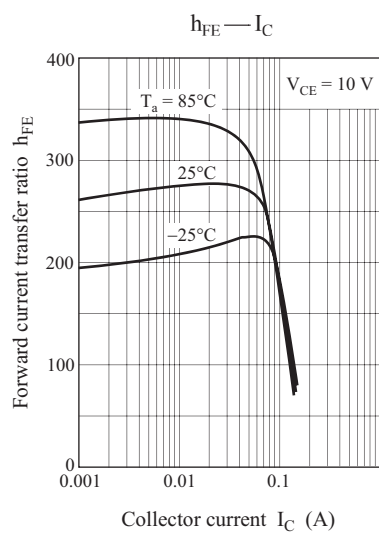
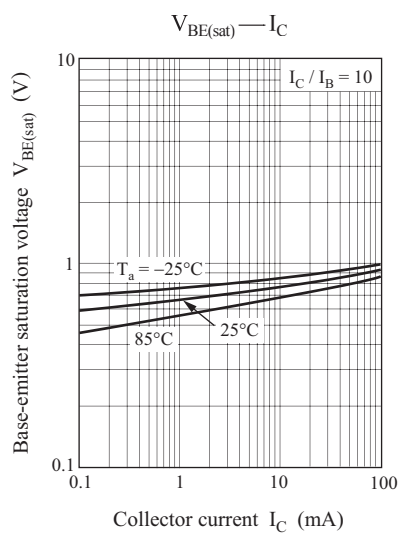
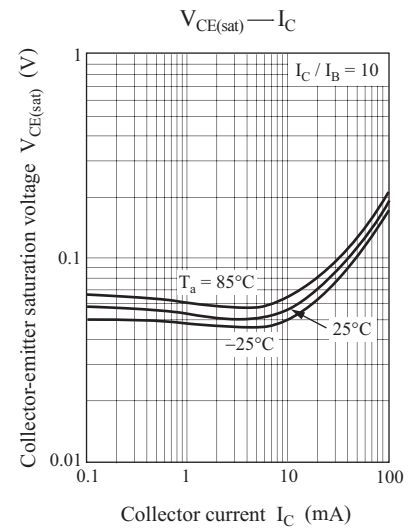
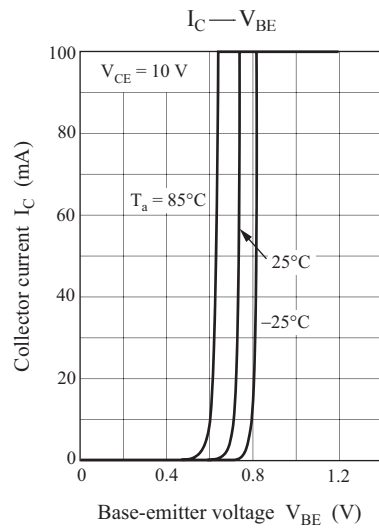
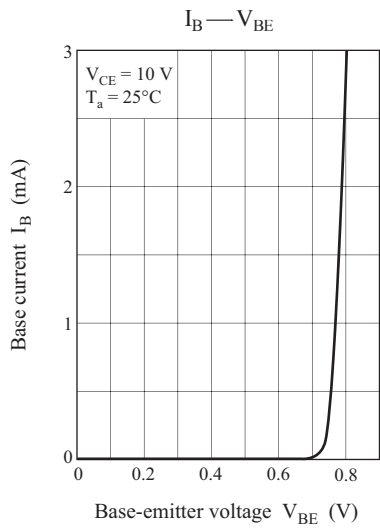
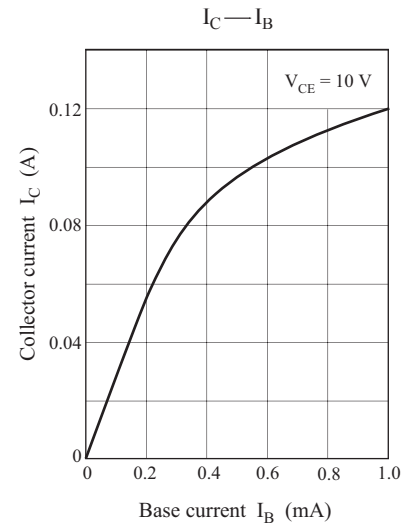
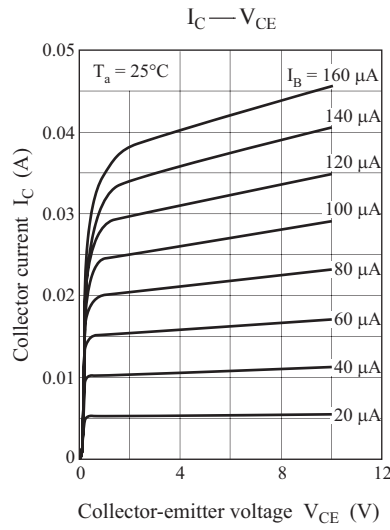
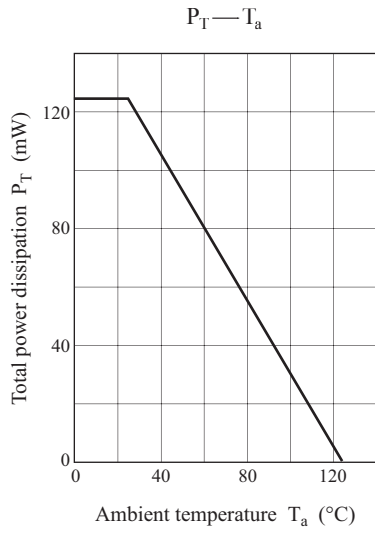


■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--|---------------|---|-----|-----|-----|---------------|
| Collector-base voltage (Emitter open) | V_{CBO} | $I_C = 10 \mu\text{A}, I_E = 0$ | 60 | | | V |
| Collector-emitter voltage (Base open) * | V_{CEO} | $I_C = 2 \text{ mA}, I_B = 0$ | 50 | | | V |
| Emitter-base voltage (Collector open) | V_{EBO} | $I_E = 10 \mu\text{A}, I_C = 0$ | 7 | | | V |
| Collector-base cutoff current (Emitter open) | I_{CBO} | $V_{CB} = 20 \text{ V}, I_E = 0$ | | | 0.1 | μA |
| Collector-emitter cutoff current (Base open) | I_{CEO} | $V_{CE} = 10 \text{ V}, I_B = 0$ | | | 100 | μA |
| Forward current transfer ratio | h_{FE} | $V_{CE} = 10 \text{ V}, I_C = 2 \text{ mA}$ | 180 | | 390 | — |
| Collector-emitter saturation voltage | $V_{CE(sat)}$ | $I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$ | | | 0.3 | V |
| Collector output capacitance (Common base, input open circuited) | C_{ob} | $V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ | | 3.5 | | pF |
| Transition frequency | f_T | $V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$ | | 150 | | MHz |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Pulse measurement



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